

MAY 01 2007

- 6 -

Application No. 10/801,542
Docket No. 74075-2717**REMARKS**

The above amendment with the following remarks is submitted to be fully responsive to the Office Action of February 1, 2007. Reconsideration of this application in light of the amendment and the allowance of this application are respectfully requested.

Claims 1-16 were pending in the present application prior to the above amendment. In response to the Office Action, claims 5 and 6 are amended to correct a typographical error. Therefore, claims 1-16 are now pending in the present application and are believed to be in proper condition for allowance.

Referring now to the Office Action, claims 1, 4, 7, 10-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura et al. (US 6,670,773). Claims 2, 5, 8, are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura as applied to claims 2, 4, 7 above, and further in view of Sivan (U.S. 5,229,310). Claims 3, 6, 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura as applied to claims 2, 4, 7, above, and further in view of Gosain et al. (U.S. 5,953,595).

The independent claims 1, 4, 7, 13, 14, 15, and 16 have been rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura. The Examiner asserts that Nakamura discloses a similar invention regarding the absolute value of the fluctuation rate of an ON current in a saturation region. Applicants respectfully disagree.

Applicants note the well-known fact that the fluctuation of the ON current is larger in the saturated area than that in the linear area. Nakamura clearly describes this fact. For example, Nakamura discloses that the polycrystalline silicon TFT tends to show a significant fluctuation from element to element in the Vg-Is current characteristics in the saturation area (see, e.g., lines 28-35 in column 2). In a similar way, in column 2 lines 37-43, Nakamura discloses that, when the TFT is driven in a linear area, the fluctuation that is observed in the saturation area does not affect the TFT strongly. In this paragraph, Nakamura does not disclose that the absolute value of a fluctuation rate of an ON current is not much experienced in the case of the saturated region, but Nakamura does disclose that the fluctuation is not so much experienced in the case of the linear region compared with the case of the saturated area. Therefore, the TFT is used in the linear region in most cases as described by Nakamura (see, lines 36-41 in column 2).

- 7 -

Application No. 10/801,542
Docket No. 74075-2717

In contrast, in the present invention, the driving TFT is operated in the saturated region as shown in the independent claims 1, 4, 7, and 13-15 (see, e.g., paragraph [0044]) in which the fluctuation of the ON current is generally larger than that in the linear region. The present invention as claimed focuses on the fluctuation rate of the ON current in the saturation region, which is the opposite of the use of the device of Nakamura. Therefore, Applicants believe that it is not obvious for one of ordinary skill in the art at the time to conceive the present invention from the invention disclosed in Nakamura.

Because Nakamura does not disclose or suggest operating the TFT in the saturated region "wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%", as is claimed in independent claims 1, 4, 7, 13, 14, 15, and 16, Applicants respectfully request the Examiner withdraw the rejection of these claims. Because dependent claims 2, 3, 5, 6, and 8-12 depend from the independent claims, Applicants request the Examiner withdraw the rejection of these claims also.

In view of the foregoing, it is submitted that the present application is in condition for allowance and a notice to that effect is respectfully requested. However, if any issue remains after considering this response, the Examiner is invited to call the undersigned to expedite the prosecution and work out any such issue by telephone.

Respectfully submitted,

Donald R. Studebaker
Registration No. 32,815NIXON PEABODY LLP
401 9th Street, N.W., Suite 900
Washington, D.C. 20004-2128
(202) 585-8000
(202) 585-8080 (Fax)
Customer No. 22204

Dated: May 1, 2007